Agne Johannessen

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/3190620/publications.pdf

Version: 2024-02-01

1163117 996975 27 239 8 15 citations g-index h-index papers 27 27 27 222 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Imaging the dephasing of spin wave modes in a square thin film magnetic element. Physical Review B, 2004, 69, .	3.2	59
2	Anisotropy, damping, and coherence of magnetization dynamics in a 10 \hat{l} 4m square Ni81Fe19 element. Applied Physics Letters, 2003, 82, 3065-3067.	3.3	52
3	A Design Approach for High-Q FBARs With a Dual-Step Frame. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2018, 65, 1717-1725.	3.0	17
4	Dependence of anisotropy and damping on shape and aspect ratio in micron sized Ni81Fe19 elements. Journal of Applied Physics, 2004, 95, 6998-7000.	2.5	12
5	Impurity-related photoluminescence line shape asymmetry in GaAs/AlAs multiple quantum wells: Fractional-dimensional space approach. Journal of Applied Physics, 2010, 107, .	2.5	11
6	Design of high-Q Thin Film Bulk Acoustic resonator using dual-mode reflection. , 2014, , .		10
7	The impact of area on BAW resonator performance and an approach to device miniaturization. Ultrasonics, 2019, 94, 92-101.	3.9	10
8	Enhanced exciton photoluminescence in the selectively Si-doped GaAs/AlxGa1â^'xAs heterostructures. Journal of Applied Physics, 2010, 108, 063522.	2.5	9
9	Observation of incoherent picosecond magnetisation dynamics in micron sized Ni81Fe19 elements by time resolved scanning Kerr effect microscopy. IET Science, Measurement and Technology, 2003, 150, 260-263.	0.7	8
10	The Characterisation and Quantification of Immobilised Concanavalin A on Quartz Surfaces Based on The Competitive Binding to Glucose and Fluorescent Labelled Dextran. Applied Sciences (Switzerland), 2019, 9, 318.	2.5	8
11	Interactions in magnetic arrays for storage and computation. Microelectronic Engineering, 2001, 57-58, 975-979.	2.4	6
12	Shape-dependent anisotropy and damping of picosecond magnetisation dynamics in a micron sized Ni81Fe19 element. Journal of Magnetism and Magnetic Materials, 2004, 272-276, 2121-2122.	2.3	6
13	Photoluminescence characterisation of GaAs/AlGaAs structures designed for microwave and terahertz detectors. Lithuanian Journal of Physics, 2011, 51, 330-334.	0.4	6
14	Light emission lifetimes in p-type \hat{l} -doped GaAs/AlAs multiple quantum wells near the Mott transition. Journal of Applied Physics, 2012, 112, 043105.	2.5	5
15	Behaviour of optical transitions in GaAs/AlAs with highly Be Î-doped MQWs. Lithuanian Journal of Physics, 2005, 45, 201-206.	0.4	5
16	Enhanced light emission in nanostructures. Lithuanian Journal of Physics, 2011, 51, 292-302.	0.4	4
17	Signal Amplification of a Gravimetric Glucose Biosensor Based on the Concanavalin A–Dextran Affinity Assay. IEEE Sensors Journal, 2021, 21, 4391-4404.	4.7	3
18	Excitonic photoluminescence quenching by impact ionization of excitons and donors inGaAs/Al0.35Ga0.65Asquantum wells with an in-plane electric field. Physical Review B, 2000, 62, 15871-15878.	3.2	2

#	Article	IF	CITATIONS
19	Lorentz microscopy analysis of arrays of rhombic elements. IEEE Transactions on Magnetics, 2003, 39, 2672-2674.	2.1	2
20	Design of a Love wave mode device for use in a microfabricated glucose sensor. , 2016, , .		2
21	Peculiarities of photoluminescence of vertical n +/n-GaAs/Al0.25Ga0.75As MBE- and MOCVD-grown structures designed for microwave detectors. Applied Physics A: Materials Science and Processing, 2015, 120, 1133-1140.	2.3	1
22	Improvement of methods in analyzing the propagation of plate waves in FBARs. , 2016, , .		1
23	Influence of Electric Field on Photoluminescence Quenching in GaAs/AlGaAs Quantum Wells. Materials Science Forum, 1999, 297-298, 253-256.	0.3	O
24	<code><title>Phonon</code> sidebands in photoluminescence of beryllium <math display="inline">\hat{l}</math> -doped GaAs/AlAs multiple quantum wells <code></title>.</code> , 2006, , .		0
25	Dynamic photoluminescence studies of vertical n+/n-GaAs/Al0.2Ga0.8As structures designed for microwave electronics. Physica Scripta, 2013, 87, 065701.	2.5	O
26	The Increase of Radiative Lifetime of Free Excitons in Selectively Si-doped GaAs/AlxGa1-xAs Heterostructures. Medziagotyra, 2014, 20, .	0.2	0
27	Photoluminescence lifetimes in GaAs/Al _{0.3} Ga _{0.7} As structures designed for microwave and terahertz detectors. Lithuanian Journal of Physics, 2013, 53, 119-126.	0.4	O